

SPTECH Silicon PNP Power Transistors

2SB555

DESCRIPTION

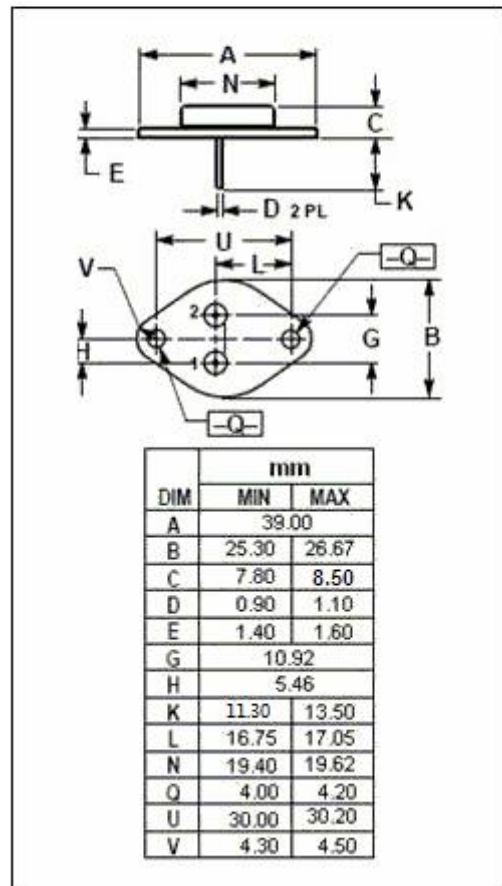
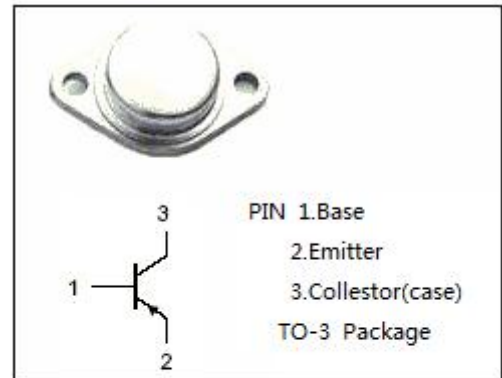
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -140V(\text{Min})$
- High Power Dissipation-
: $P_C = 80W(\text{Max})@T_C = 25^\circ\text{C}$
- Complement to Type 2SD425

APPLICATIONS

- Designed for power amplifier applications.
- Recommended for 80W high-fidelity audio frequency amplifier output stage.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-140	V
V_{CEO}	Collector-Emitter Voltage	-140	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-12	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	80	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistors**2SB555****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; I _B = 0	-140			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -10mA; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -7A; I _B = -0.7A			-3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -7A; V _{CE} = -5V			-2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V; I _E = 0			-0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.1	mA
h _{FE}	DC Current Gain	I _C = -2A; V _{CE} = -5V	40		140	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		330		pF
f _T	Current-Gain—Bandwidth Product	I _C = -2A; V _{CE} = -5V		6		MHz

◆ h_{FE} Classifications

R	O
40-80	70-140